

	Type	Hits	Search Text	DBs	Time Stamp
1	IS&R	672	(257/317,510).CCLS.	USPAT; US-PGPUB	2002/12/04 12:57
2	BRS	91	((257/317,510).CCLS.) and @pd>20020617	USPAT; US-PGPUB	2002/12/04 12:58

	Document ID	Pages	Title	Current OR	Current XRef	Invent r
1	US 20020093073 A1	38	Semiconductor device having two-layered charge storage electrode	257/510		Mori, Seiichi et al.
2	US 6459121 B1	29	Method for producing non-volatile semiconductor memory device and the device	257/315	257/317; 257/321; 438/257	Sakamoto, Osamu et al.
3	US 6448606 B1	14	Semiconductor with increased gate coupling coefficient	257/315	257/317; 257/510; 257/515; 438/296	Yu, Allen S. et al.